

KK1000-FAST SWITCHING THYRISTOR

1800-2000 V_{DRM}

HIGH POWER THYRISTOR FOR INVERTER APPLICATION

Features:

- . All Diffused Structure
- . Amplifying Gate Configuration
- . Blo]

ELECTRICAL CHARACTERISTICS AND RATINGS KK1000-FAST SWITCHING THYRISTOR

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		150		mA	$V_D=12V; R_L=30\Omega; T_j=+25^\circ C$
Gate- trigger voltage	V_{GT}	0.70	2.5		V	V_{GT}

